

Figure 1 – Schematical representation of the (a) Ga₂O₃ and (b) GaN ALD cycles.

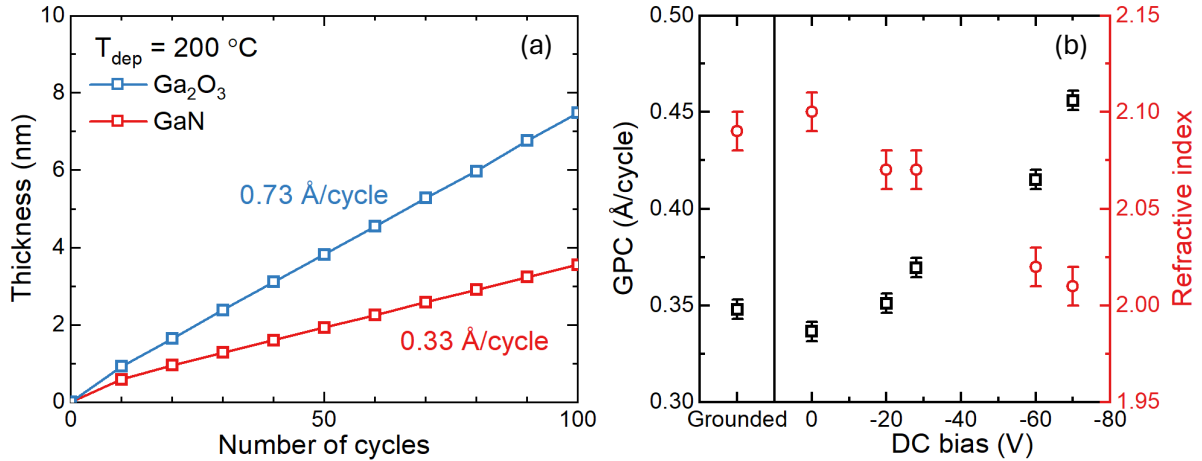


Figure 2 – (a) Thickness as function of number of cycles, showing linear growth behaviour, and (b) the effect of rf substrate biasing on GPC and refractive index of GaN.

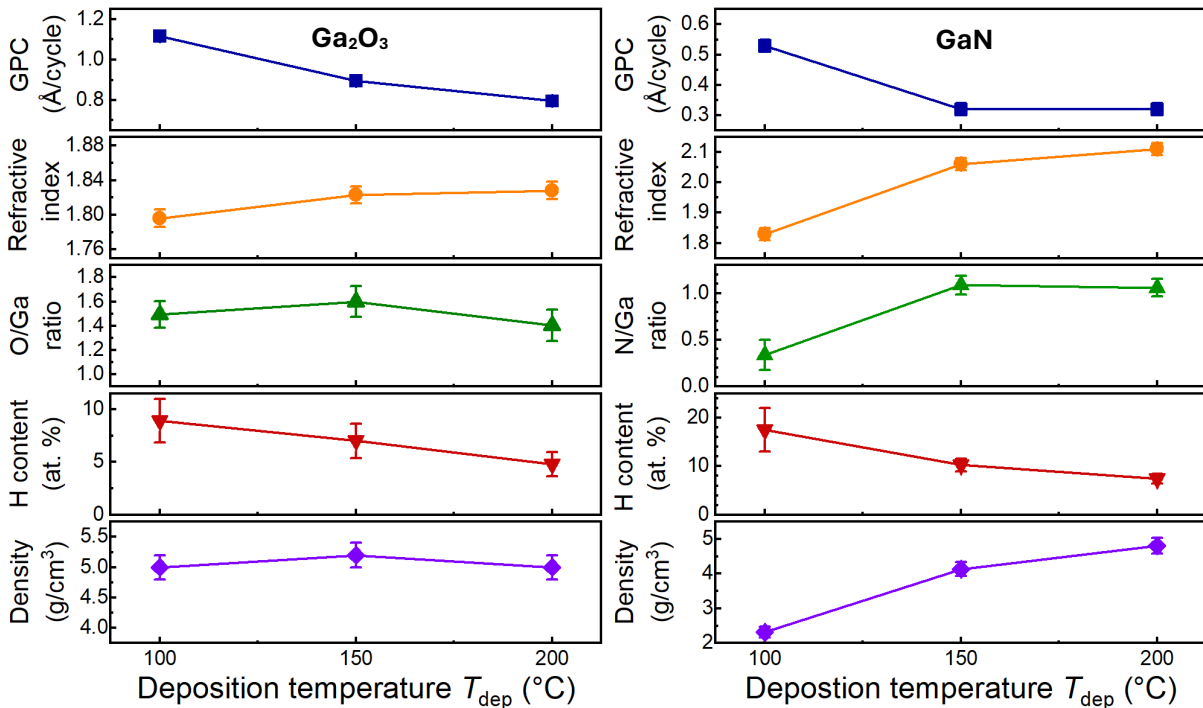


Figure 3 – Properties of Ga₂O₃ and GaN as function of deposition temperature (T_{dep}).